

MOSFETs Silicon P-Channel MOS (U-MOSVI)

# **TJ15P04M3**

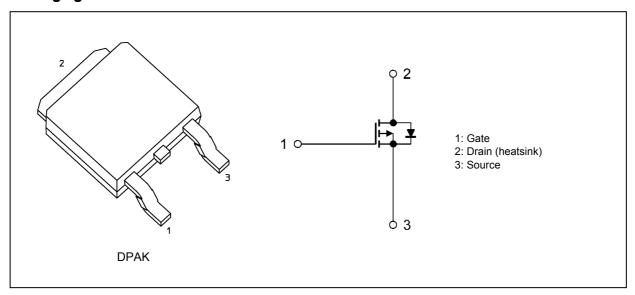
#### 1. Applications

- · Motor Drivers
- · Power Management Switches

#### 2. Features

- (1) Low drain-source on-resistance:  $R_{DS(ON)} = 28 \text{ m}\Omega$  (typ.) ( $V_{GS} = -10 \text{ V}$ )
- (2) Low leakage current:  $I_{DSS} = -10 \,\mu\text{A} \,(\text{max}) \,(V_{DS} = -40 \,\text{V})$
- (3) Enhancement mode:  $V_{th}$  = -0.8 to -2.0 V ( $V_{DS}$  = -10 V,  $I_D$  = -0.1 mA)

#### 3. Packaging and Internal Circuit



## 4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

Characteristics			Symbol	Rating	Unit
Drain-source voltage			$V_{DSS}$	-40	V
Gate-source voltage			V <sub>GSS</sub>	±20	
Drain current (DC)		(Note 1)	I <sub>D</sub>	-15	Α
Drain current (pulsed)		(Note 1)	I <sub>DP</sub>	-45	
Power dissipation	(T <sub>c</sub> = 25°C)		$P_{D}$	29	W
Single-pulse avalanche energy		(Note 2)	E <sub>AS</sub>	29	mJ
Single-pulse avalanche current			I <sub>AS</sub>	-15	Α
Channel temperature			T <sub>ch</sub>	150	°C
Storage temperature			T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production

2010-01



#### 5. Thermal Characteristics

Characteristics		Max	Unit
Channel-to-case thermal resistance	R <sub>th(ch-c)</sub>	4.3	°C/W
Channel-to-ambient thermal resistance	R <sub>th(ch-a)</sub>	125	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD}$  = -32 V,  $T_{ch}$  = 25°C (initial), L = 100  $\mu H$ ,  $R_{G}$  = 25  $\Omega$ ,  $I_{AS}$  = -15 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



#### 6. Electrical Characteristics

#### 6.1. Static Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_		±0.1	μА
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = -40 V, V <sub>GS</sub> = 0 V	-	_	-10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	-40			٧
Drain-source breakdown voltage (Note 3)	V <sub>(BR)DSX</sub>	$I_D$ = -10 mA, $V_{GS}$ = 10 V	-30			
Gate threshold voltage	$V_{th}$	$V_{DS} = -10 \text{ V}, I_D = -0.1 \text{ mA}$	-0.8		-2.0	
Drain-source on-resistance	R <sub>DS(ON)</sub>	$V_{GS} = -4.5 \text{ V}, I_D = -7.5 \text{ A}$	1	37	48	mΩ
		V <sub>GS</sub> = -10 V, I <sub>D</sub> = -7.5 A	_	28	36	

Note 3: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.

#### 6.2. Dynamic Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	1100	_	pF
Reverse transfer capacitance	C <sub>rss</sub>		_	130	_	
Output capacitance	C <sub>oss</sub>		_	170	_	
Switching time (rise time)	t <sub>r</sub>	See Figure 6.2.1.	_	11	_	ns
Switching time (turn-on time)	t <sub>on</sub>		_	19	_	
Switching time (fall time)	t <sub>f</sub>		_	42	_	
Switching time (turn-off time)	t <sub>off</sub>			170	_	

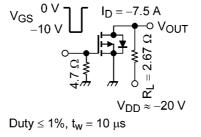


Fig. 6.2.1 Switching Time Test Circuit

### 6.3. Gate Charge Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	$Q_g$	$V_{DD} \approx -32 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -15 \text{ A}$	_	26		nC
Gate-source charge 1	Q <sub>gs1</sub>			6.7		
Gate-drain charge	$Q_{gd}$			2.5		

## 6.4. Source-Drain Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (Note 4)	I <sub>DRP</sub>	_	_	-	-45	Α
Diode forward voltage	$V_{DSF}$	I <sub>DR</sub> = -15 A, V <sub>GS</sub> = 0 V	_	_	1.2	V

Note 4: Ensure that the channel temperature does not exceed 150°C.



## 7. Marking

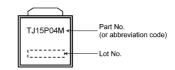


Fig. 7.1 Marking

#### 8. Characteristics Curves (Note)

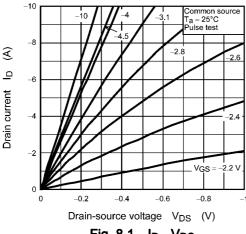


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>

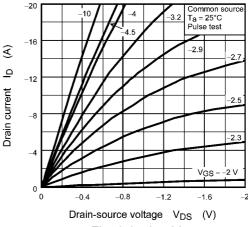


Fig. 8.2 I<sub>D</sub> - V<sub>DS</sub>

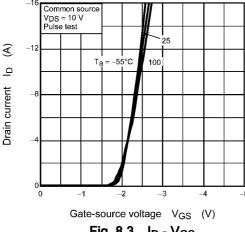


Fig. 8.3  $I_D$  -  $V_{GS}$ 

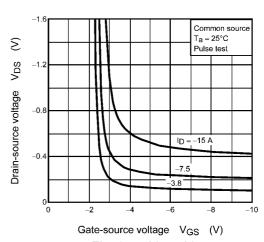


Fig. 8.4 V<sub>DS</sub> - V<sub>GS</sub>

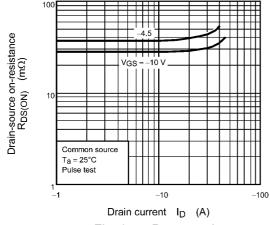


Fig. 8.5 R<sub>DS(ON)</sub> - I<sub>D</sub>

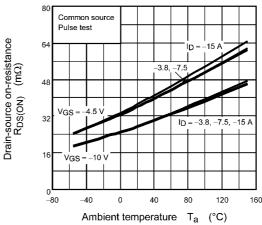
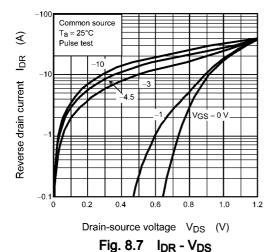
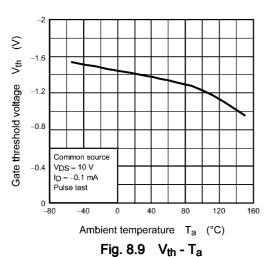
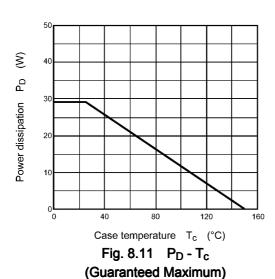


Fig. 8.6 R<sub>DS(ON)</sub> - T<sub>a</sub>







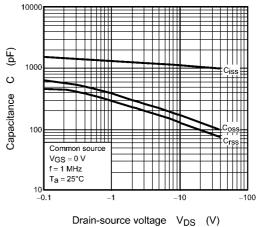


Fig. 8.8 Capacitance - V<sub>DS</sub>

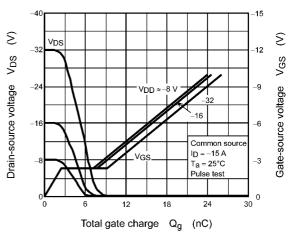


Fig. 8.10 Dynamic Input/Output Characteristics

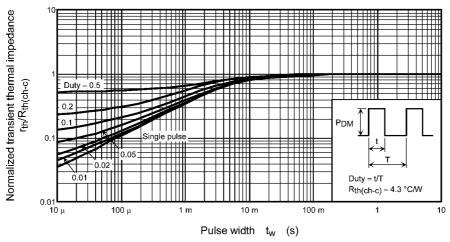


Fig. 8.12  $r_{th}/R_{th(ch-c)} - t_w$  (Guaranteed Maximum)

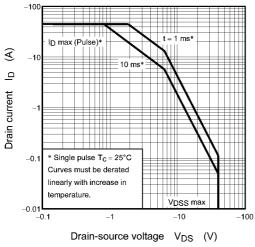


Fig. 8.13 Safe Operating Area (Guaranteed Maximum)

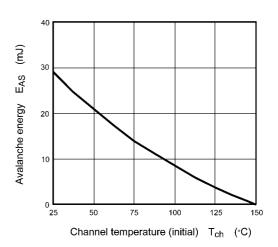


Fig. 8.14 E<sub>AS</sub> - T<sub>ch</sub> (Guaranteed Maximum)

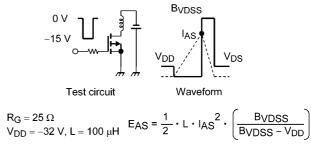


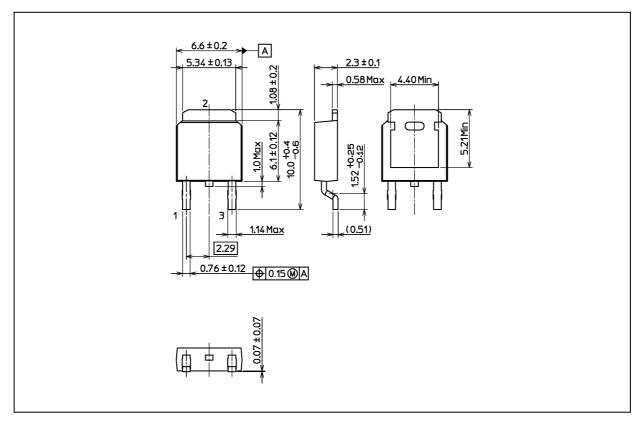
Fig. 8.15 Test Circuit/Waveform

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



#### **Package Dimensions**

Unit: mm



Weight: 0.36 g (typ.)

	Package Name(s)
TOSHIBA: 2-7K1S	
Nickname: DPAK	



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